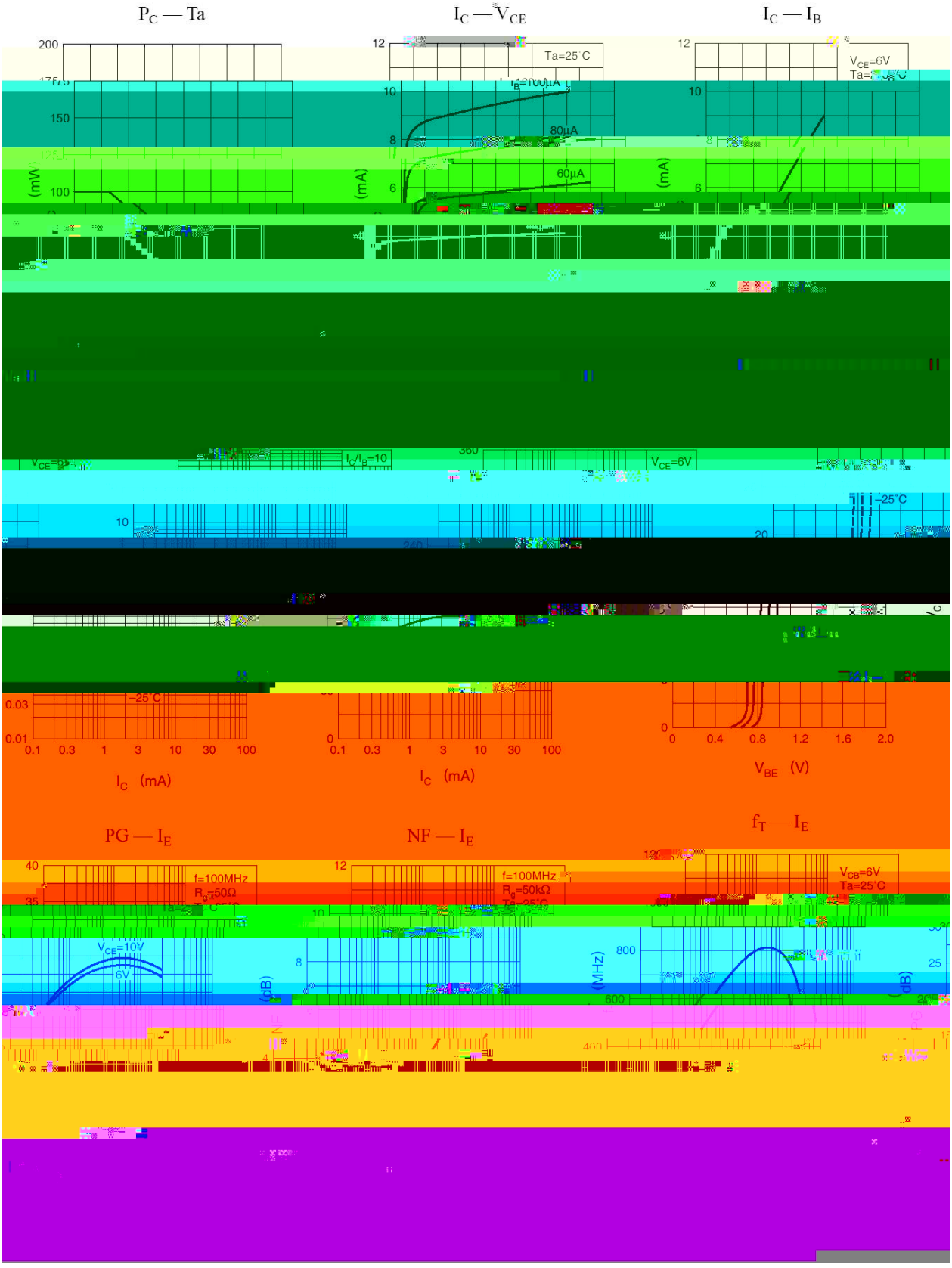
/ Absolute Maximum Ratings(Ta=25)

v Ѽ Parameter	ч N Symbol	Ѽ Ө Rating	D Ч Unit
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	3.0	V
Collector Current	I_C	15	mA
Collector Power Dissipation	P_C	100	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

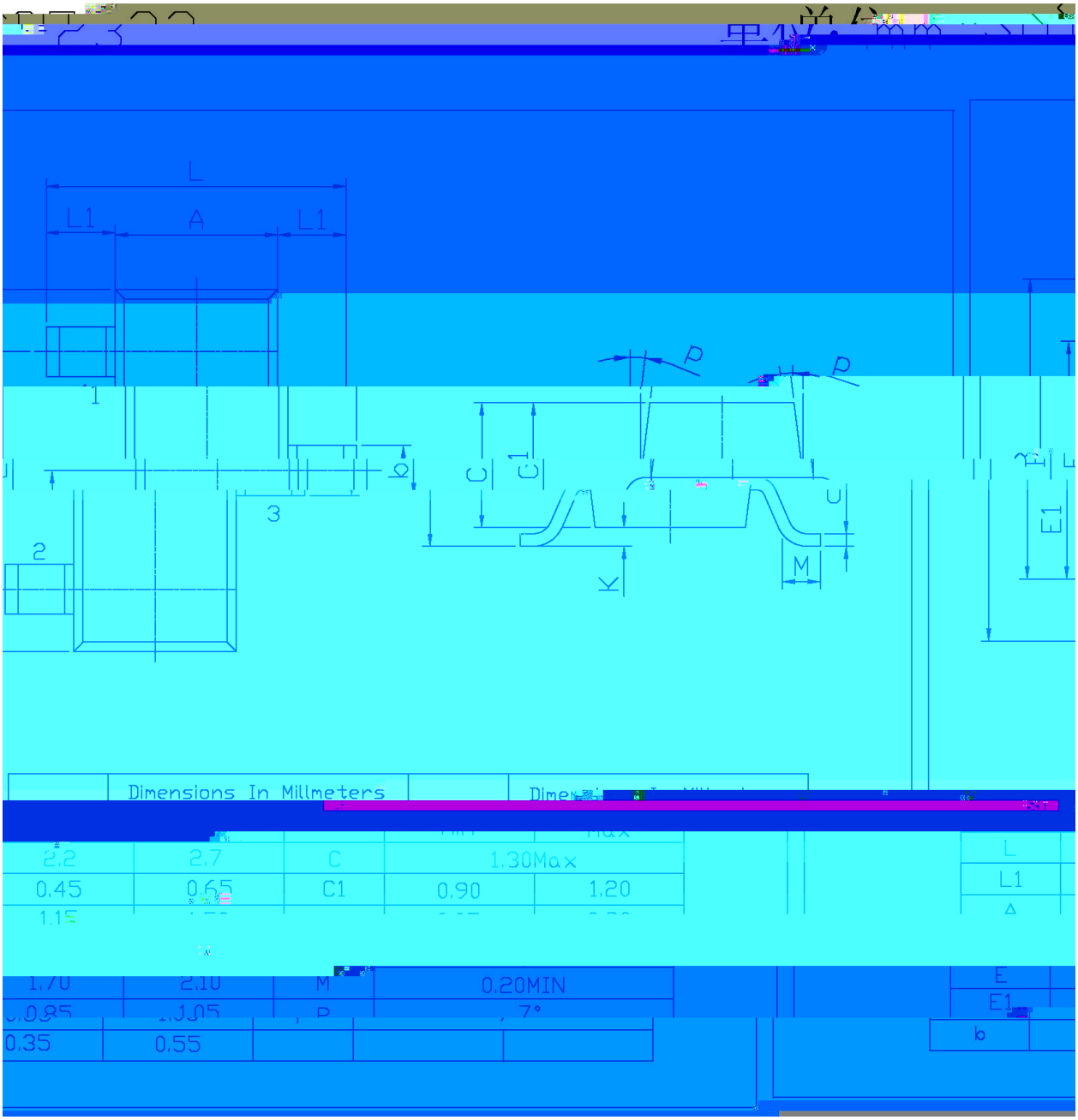
/ Electrical Characteristics(Ta=25)

v Ѽ Parameter	ч N Symbol	Ш :ϯ Ţ Test Conditions	ѡ ṇ Ө Min	Ɛ ʒ Ө Typ	ѡ ᶻ Ө Max	D Ч Unit
Collector- Base Breakdown Voltage	V_{CBO}	I_C=10μA	30			V
Emitter-Base Breakdown Voltage	V_{EBO}	I_E=10μA	3.0			V
DC Current Gain	h_{FE}	V_{CE}=6.0V I_c=1.0mA	40		260	
Transition Frequency	f_T	V_{CB}=6.0V I_c=1.0mA	450	650		MHz
Base to Emitter Voltage	V_{BE}	V_{CB}=6.0V I_c=1.0mA		0.72		V
Common Emitter Reverse Transfer Capacitance	C_{re}	V_{CB}=6.0V I_C=1.0mA f=10.7MHz		0.8	1.0	PF
Power Gain	P_G	V_{CB}=6.0V I_C=1.0mA f=100MHz		24		dB
Noise Figure	NF	V_{CB}=6.0V I_C=1.0mA f=100MHz		3.3		dB

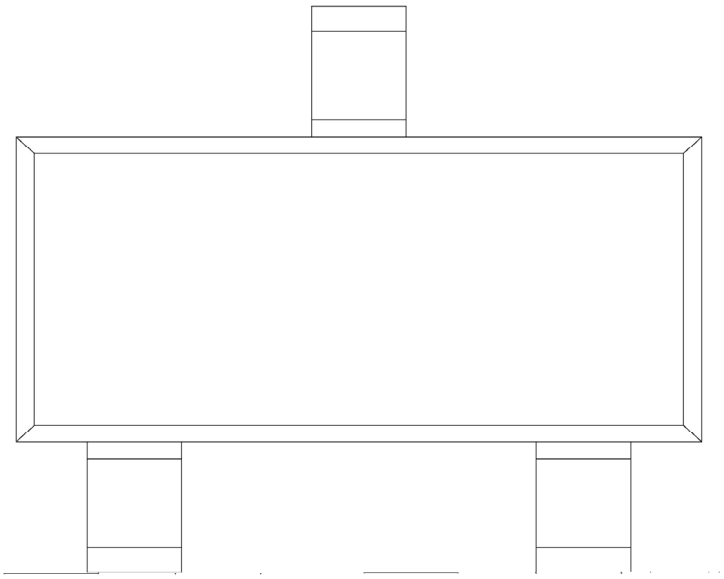
/ Electrical Characteristic Curve



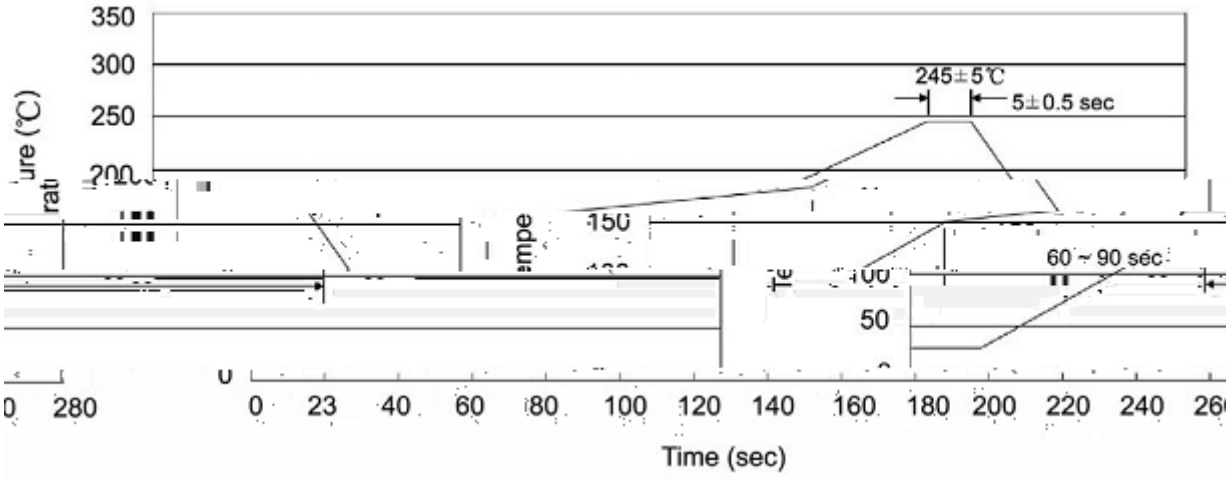
/ Package Dimensions



/ Marking Instructions



( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



ب ˝ χ

1 ⅃ ♬ □ ỷ 25 Ḱ 150 ɫ ı `H ڑ 60 Ḱ 90sec;

2 Š Ö □ ỷ 245 ° 5 ɫ ı `H ڑ ˈY ⅄ ⅉ 5 ° 0.5sec;

3 ì ˙ ⅄ ˛ ɔ ɯ ỷ ⅉ 2 Ḱ 10 ɫ /sec.

Note:

1.Preheating:25~150 ɫ , Time:60~90sec.

2.Peak Temp.:245 ° 5 ɫ , Duration:5 ° 0.5sec.

3.